G3R45MT17-CAL
1700 V 45 mΩ SiC MOSFET

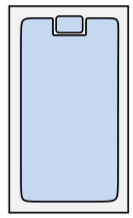
Silicon Carbide MOSFET
N-Channel Enhancement Mode

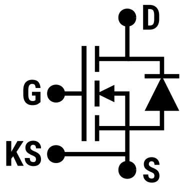
V_{DS}	=	1700 V
$R_{DS(ON)(Typ.)}$	=	45 mΩ
$I_{D (T_C = 100°C)}$	=	40 A

Features

- G3R™ Technology with +15 V Gate Drive
- Softer $R_{DS(ON)}$ v/s Temperature Dependency
- LoRing™ - Electromagnetically Optimized Design
- Smaller $R_{G(INT)}$ and Lower Q_G
- Low Device Capacitances (C_{OSS}, C_{RSS})
- Superior Cost-Performance Index
- Robust Body Diode with Low V_F and Low Q_{RR}
- Industry-Leading UIL & Short-Circuit Robustness

Bare Chip





D = Drain
G = Gate
S = Source
KS = Kelvin Source

RoHS
REACH

Advantages

- Compatible with Commercial Gate Drivers
- Low Conduction Losses at all Temperatures
- Reduced Ringing
- Faster and More Efficient Switching
- Lesser Switching Spikes and Lower Losses
- Better Power Density and System Efficiency
- Ease of Paralleling without Thermal Runaway
- Higher System Reliability

Applications

- Electric Vehicle Fast Charging
- Solar Inverters
- Traction Inverters
- Smart Grid and HVDC
- High Voltage DC-DC Converters
- Switched Mode Power Supply
- Wind Energy Converters
- Pulsed Power

Absolute Maximum Ratings (At T_C = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Drain-Source Voltage	$V_{DS(max)}$	V_{GS} = 0 V, I_D = 100 µA	1700	V	
Gate-Source Voltage (Dynamic)	$V_{GS(max)}$		-10 / +20	V	
Gate-Source Voltage (Static)	$V_{GS(op)}$	Recommended Operation	-5 / +15	V	
Continuous Forward Current	I_D	T_C = 25°C, V_{GS} = -5 / +15 V	53	A	
		T_C = 100°C, V_{GS} = -5 / +15 V	40		
		T_C = 135°C, V_{GS} = -5 / +15 V	32		
Pulsed Drain Current	$I_{D(pulse)}$	t_P ≤ 3µs, D ≤ 1%, V_{GS} = 15 V, Note 1	120	A	
Power Dissipation	P_D	T_c = 25°C	425	W	Note 2
Non-Repetitive Avalanche Energy	E_{AS}	L = 3.9 mH, I_{AS} = 17.5 A	592	mJ	
Operating and Storage Temperature	T_j , T_{stg}		-55 to 200	°C	

Note 1: Pulse Width t_P Limited by $T_{j(max)}$

Electrical Characteristics (At T_C = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values Min.	Values Typ.	Values Max.	Unit	Note
Drain-Source Breakdown Voltage	V_{DSS}	V_{GS} = 0 V, I_D = 100 µA	1700			V	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1700 V, V_{GS} = 0 V		1		µA	
Gate Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V V_{DS} = 0 V, V_{GS} = -10 V			100 -100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 30.0 mA V_{DS} = V_{GS}, I_D = 30.0 mA, T_j = 200°C	1.8	2.70 1.85		V	Fig. 9
Transconductance	g_{fs}	V_{DS} = 10 V, I_D = 35 A V_{DS} = 10 V, I_D = 35 A, T_j = 200°C		16.8 16.6		S	Fig. 4
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} = 15 V, I_D = 35 A V_{GS} = 15 V, I_D = 35 A, T_j = 200°C		45 108	62	mΩ	Fig. 5-8
Input Capacitance	C_{iss}	V_{DS} = 1000 V, V_{GS} = 0 V f = 1 MHz, V_{AC} = 25mV		3199		pF	Fig. 11
Output Capacitance	C_{oss}			86		pF	Fig. 11
Reverse Transfer Capacitance	C_{rss}			15.3		pF	Fig. 11
C_{oss} Stored Energy	E_{oss}			57		µJ	Fig. 12
C_{oss} Stored Charge	Q_{oss}			172		nC	
Effective Output Capacitance (Energy Related)	$C_{o(er)}$			114		pF	Note 3
Effective Output Capacitance (Time Related)	$C_{o(tr)}$			172		pF	Note 3
Gate-Source Charge	Q_{gs}	V_{DS} = 1000 V, V_{GS} = -5 / +15 V I_D = 35 A Per IEC607478-4		33		nC	Fig. 10
Gate-Drain Charge	Q_{gd}			37		nC	Fig. 10
Total Gate Charge	Q_g			106		nC	Fig. 10
Internal Gate Resistance	$R_{G(int)}$	f = 1 MHz, V_{AC} = 25 mV		1.3		Ω	
Turn-On Switching Energy (Body Diode)	E_{On}	T_j = 25°C; V_{GS} = -5/+15V; $R_{G(ext)}$ = 1 Ω, I_D = 35 A; V_{DD} = 1200 V		222		µJ	Fig. 18
Turn-Off Switching Energy (Body Diode)	E_{Off}			100		µJ	Fig. 18
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 1200 V, V_{GS} = -5/+15V $R_{G(ext)}$ = 1 Ω, I_D = 35 A Timing relative to V_{DS}, Resistive load		7		ns	Fig. 20
Rise Time	t_r			16		ns	Fig. 20
Turn-Off Delay Time	$t_{d(off)}$			6		ns	Fig. 20
Fall Time	t_f			10		ns	Fig. 20

**The chip technology was characterized up to 200 V/ns. The measured dV/dt was limited by measurement test setup and package.*

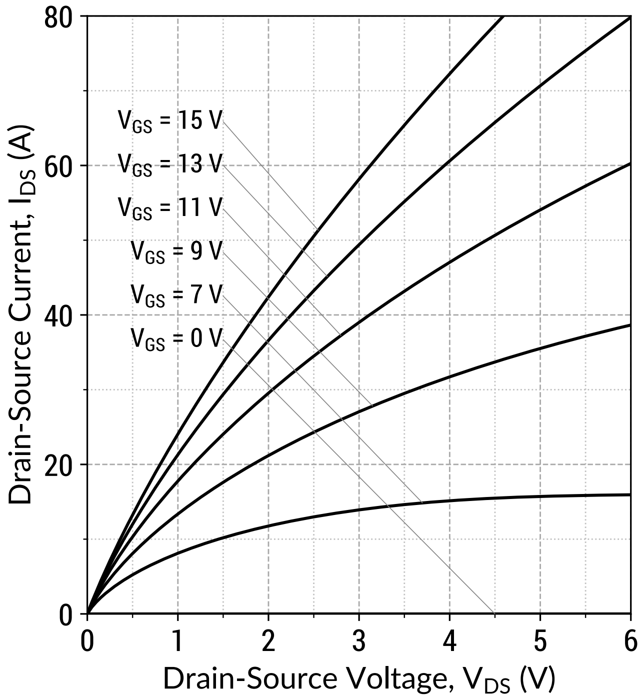
Note 2: Assuming $Rth_{JC(max)}$ = 0.41°C/W

Note 3: $C_{o(er)}$, a lumped capacitance that gives same stored energy as C_{OSS} while V_{DS} is rising from 0 to 1000V.
$C_{o(tr)}$, a lumped capacitance that gives same charging times as C_{OSS} while V_{DS} is rising from 0 to 1000V.

Reverse Diode Characteristics

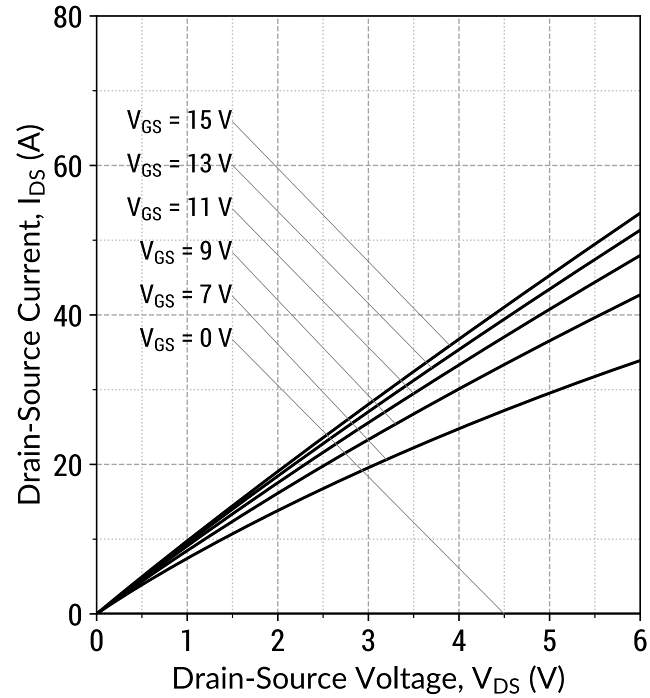
Parameter	Symbol	Conditions	Values Min.	Values Typ.	Values Max.	Unit	Note
Diode Forward Voltage	V_{SD}	V_{GS} = -5 V, I_{SD} = 17 A V_{GS} = -5 V, I_{SD} = 17 A, T_j = 200°C		4.5 4.3		V	Fig. 13-14
Continuous Diode Forward Current	I_S	V_{GS} = -5 V, T_c = 100°C	41			A	
Diode Pulse Current	$I_{S(pulse)}$	V_{GS} = -5 V, Note 1		164		A	
Reverse Recovery Time	t_{rr}	V_{GS} = -5 V, I_{SD} = 35 A, V_R = 1200 V dif/dt = 2200 A/µs, T_j = 25°C		31		ns	
Reverse Recovery Charge	Q_{rr}			305		nC	
Peak Reverse Recovery Current	I_{rrm}			8		A	
Reverse Recovery Time	t_{rr}	V_{GS} = -5 V, I_{SD} = 35 A, V_R = 1200 V dif/dt = 2200 A/µs, T_j = 200°C		56		ns	
Reverse Recovery Charge	Q_{rr}			1174		nC	
Peak Reverse Recovery Current	I_{rrm}			18		A	

Figure 1: Output Characteristics (T_j = 25°C)



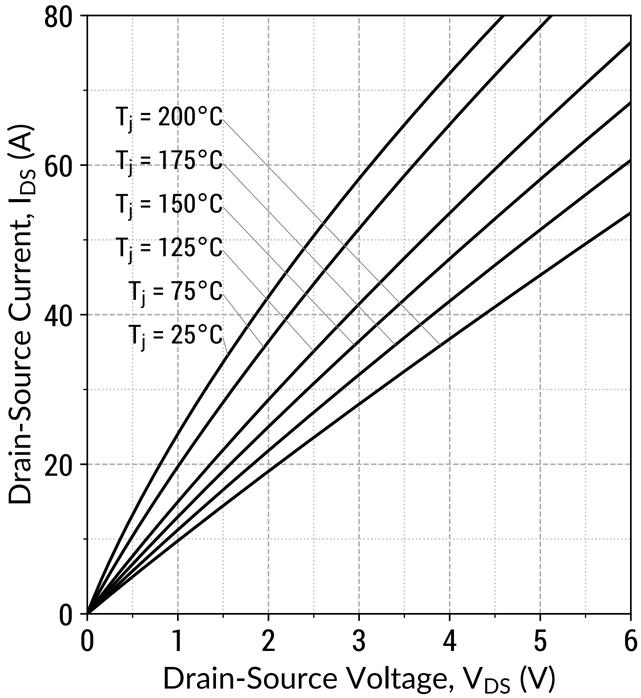
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 2: Output Characteristics (T_j = 200°C)



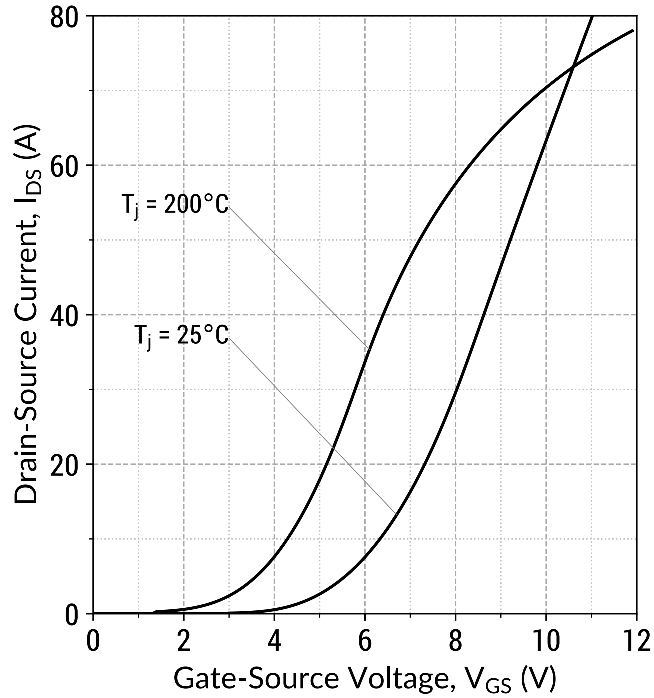
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 3: Output Characteristics (V_{GS} = 15 V)



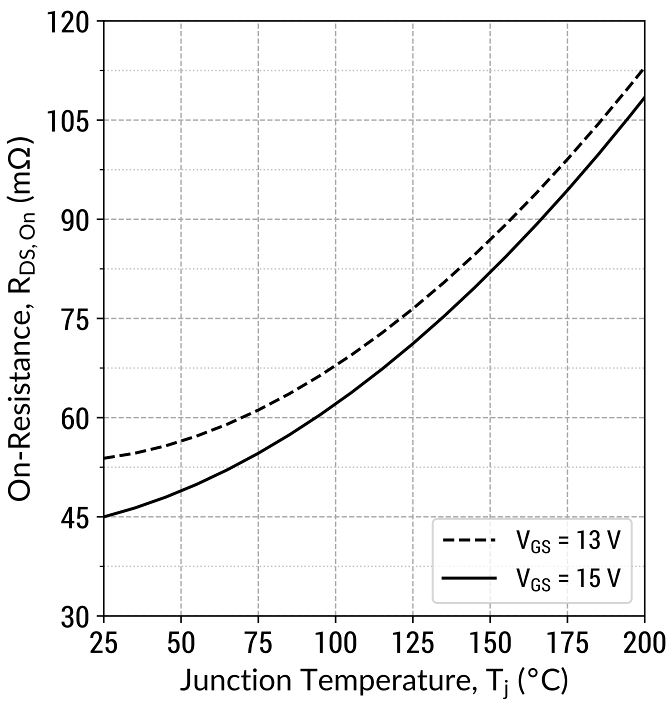
$I_D = f(V_{DS}, T_j)$; t_P = 250 µs

Figure 4: Transfer Characteristics (V_{DS} = 10 V)



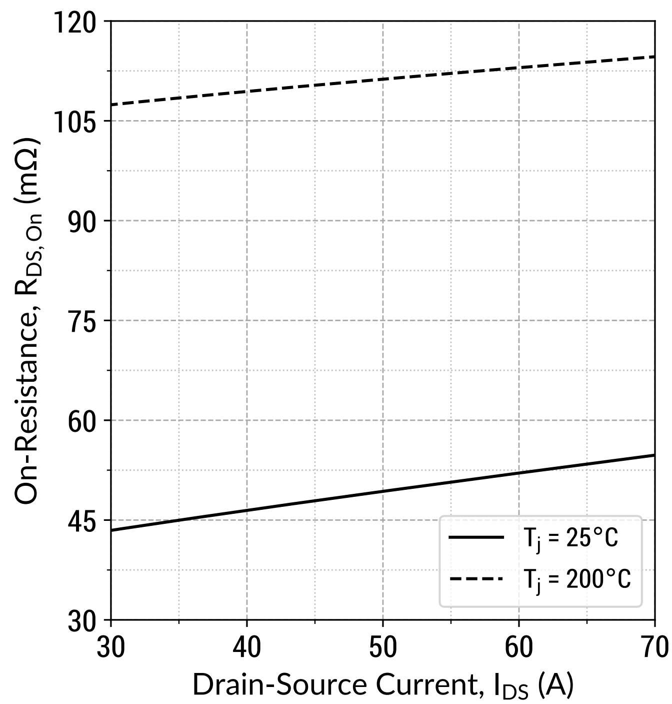
$I_D = f(V_{GS}, T_j)$; t_P = 100 µs

Figure 5: On-State Resistance v/s Temperature



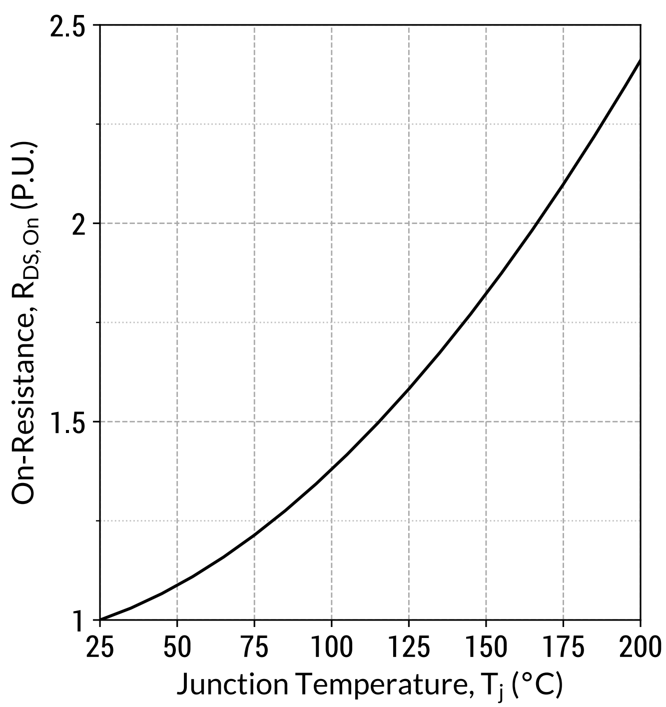
$R_{DS(ON)} = f(T_j, V_{GS})$; t_P = 250 µs; I_D = 35 A

Figure 6: On-State Resistance v/s Drain Current



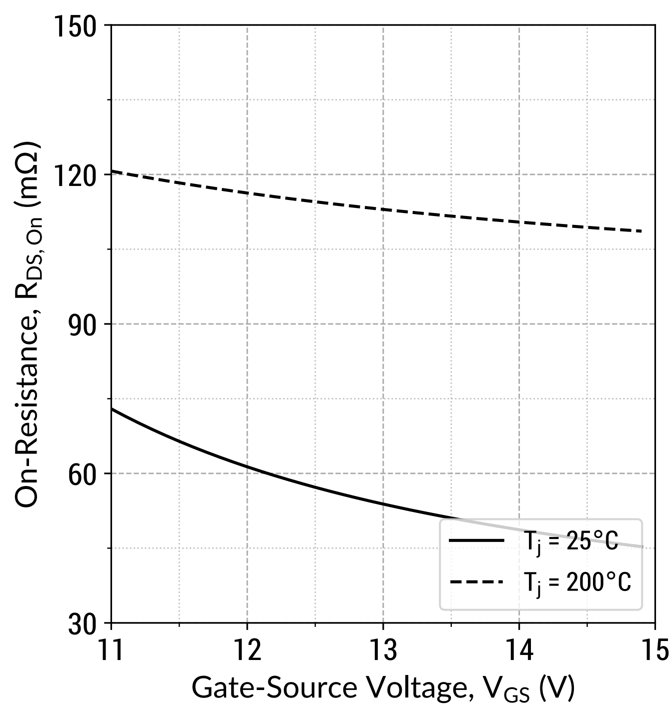
$R_{DS(ON)} = f(T_j, I_D)$; t_P = 250 µs; V_{GS} = 15 V

Figure 7: Normalized On-State Resistance v/s Temperature



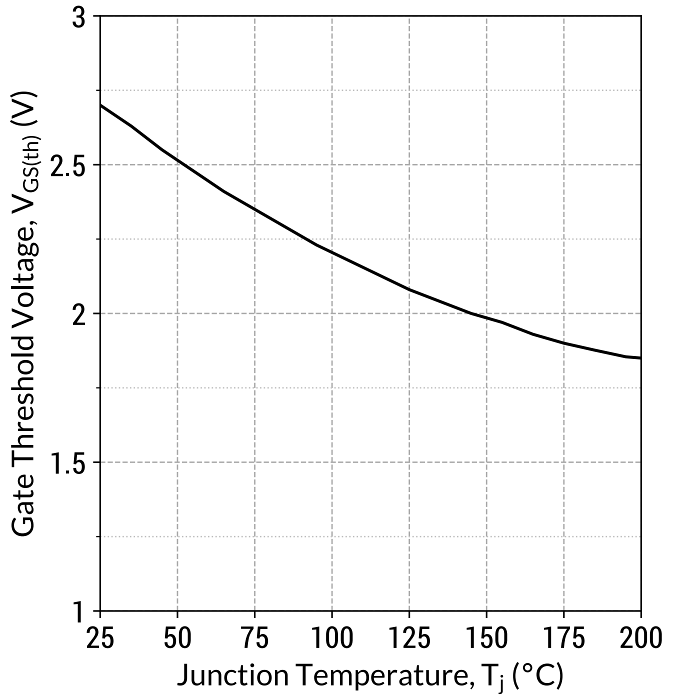
$R_{DS(ON)} = f(T_j)$; t_P = 250 µs; I_D = 35 A; V_{GS} = 15 V

Figure 8: On-State Resistance v/s Gate Voltage



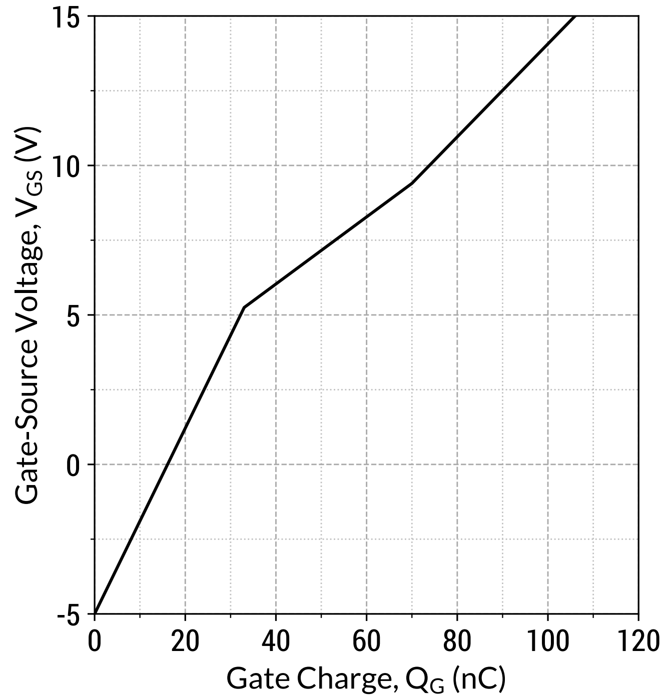
$R_{DS(ON)} = f(T_j, V_{GS})$; t_P = 250 µs; I_D = 35 A

Figure 9: Threshold Voltage Characteristics



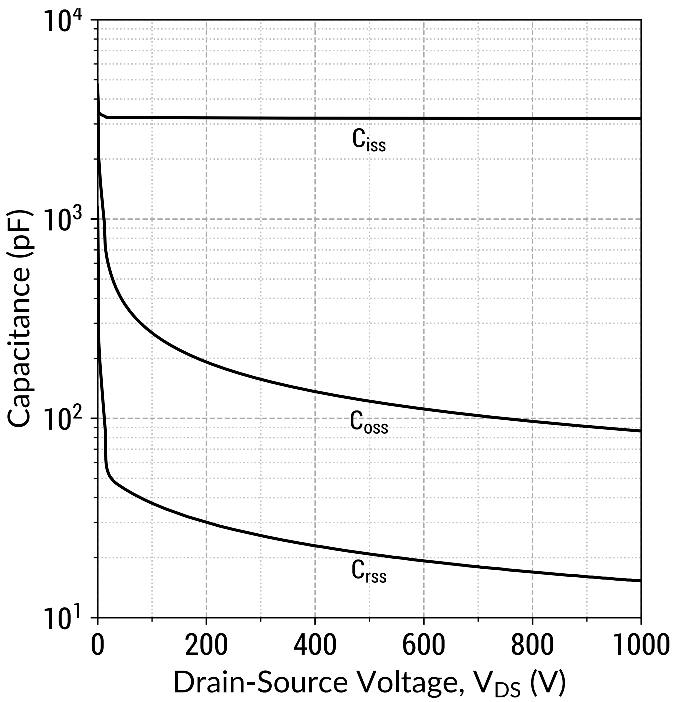
$V_{GS(th)} = f(T_j)$; $V_{DS} = V_{GS}$; $I_D = 30.0$ mA

Figure 10: Gate Charge Characteristics



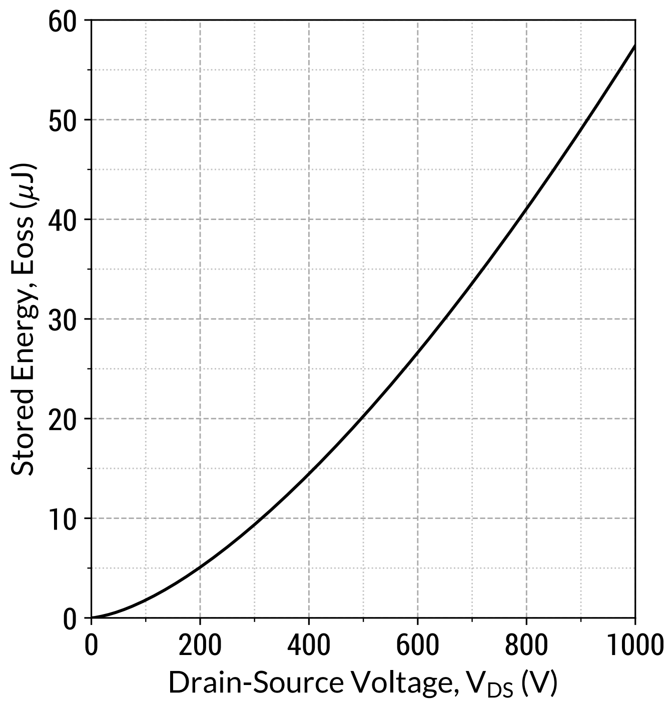
$I_D = 35$ A; $V_{DS} = 1000$ V; $T_c = 25$°C

Figure 11: Capacitance v/s Drain-Source Voltage



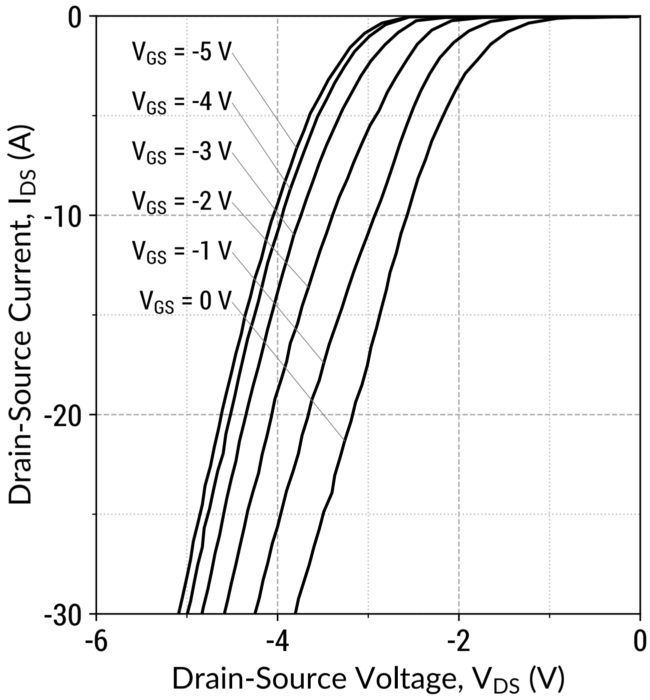
f = 1 MHz; $V_{AC} = 25$mV

Figure 12: Output Capacitor Stored Energy



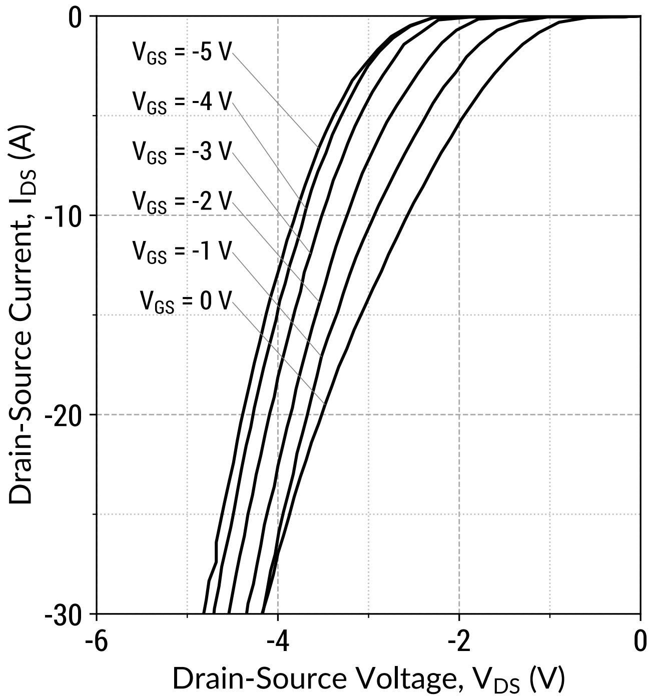
$E_{oss} = f(V_{DS})$

Figure 13: Body Diode Characteristics (T_j = 25°C)



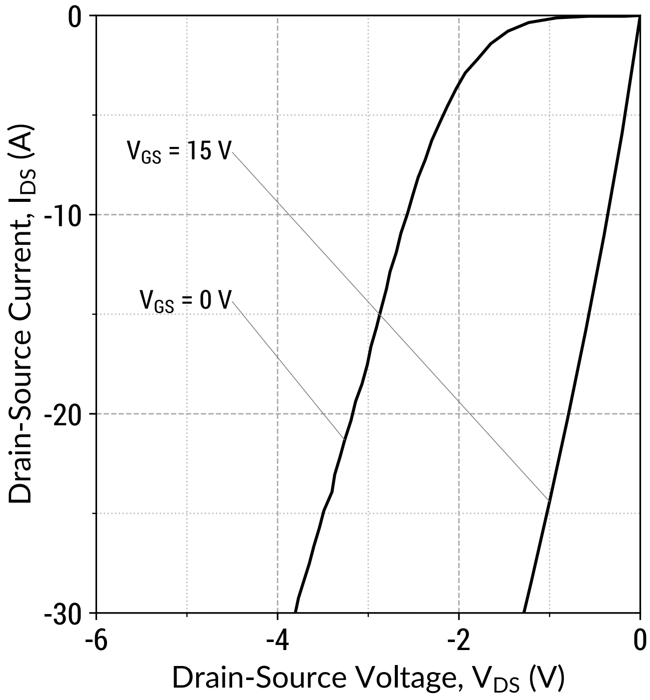
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 14: Body Diode Characteristics (T_j = 200°C)



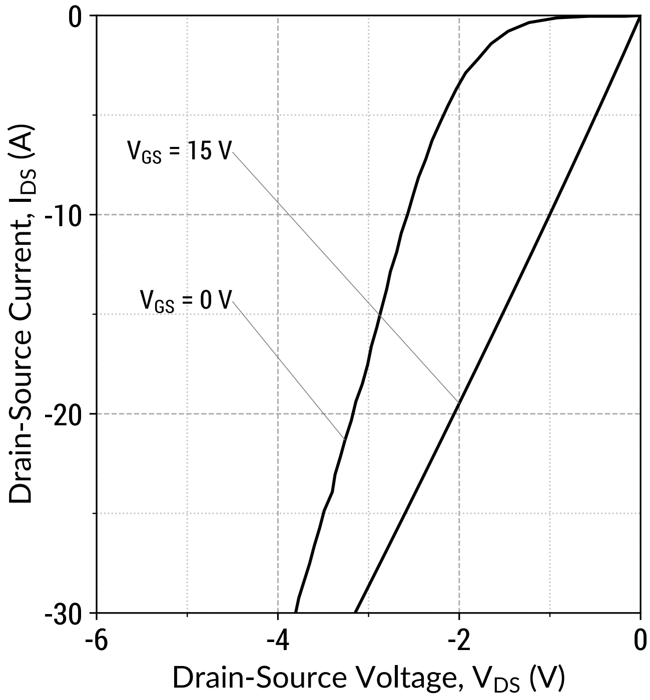
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 15: Third Quadrant Characteristics (T_j = 25°C)



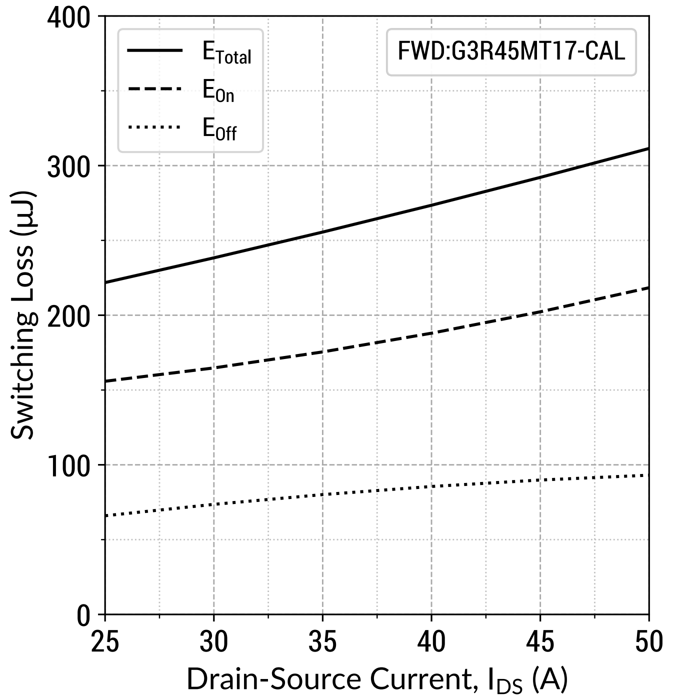
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 16: Third Quadrant Characteristics (T_j = 200°C)



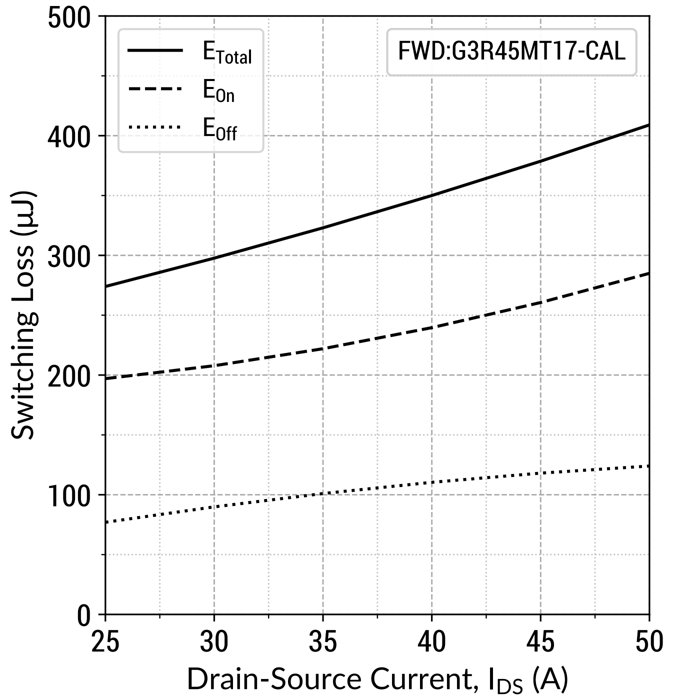
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 17: Resistive Switching Energy v/s Drain Current (V_{DD} = 1000V)



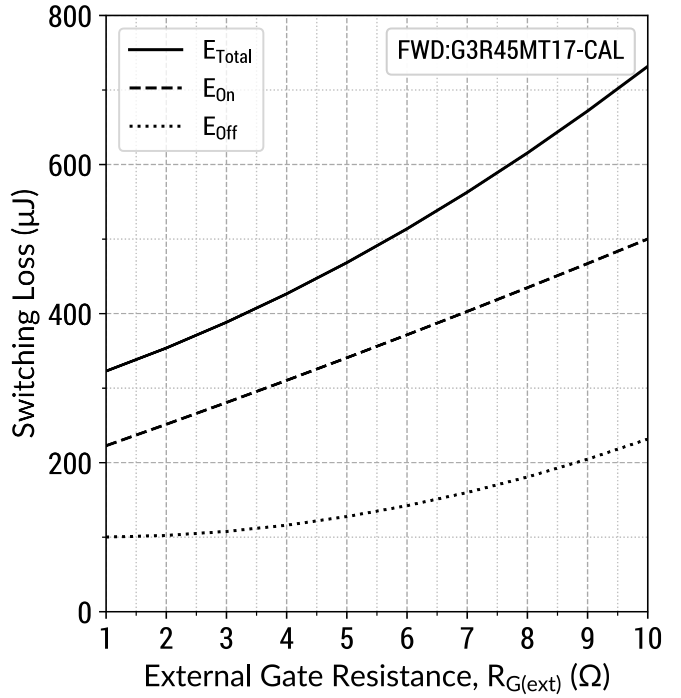
T_j = 25°C; V_{GS} = -5/+15V; $R_{G(ext)}$ = 1 Ω

Figure 18: Resistive Switching Energy v/s Drain Current (V_{DD} = 1200V)



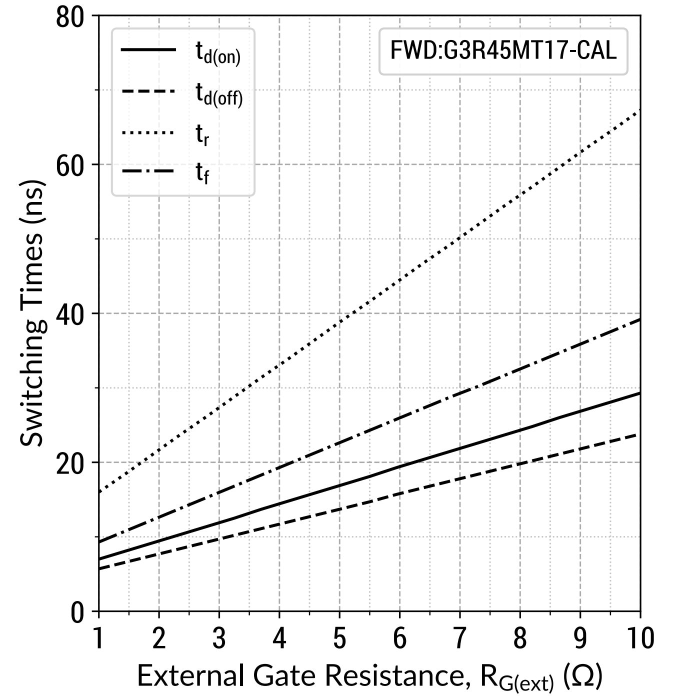
T_j = 25°C; V_{GS} = -5/+15V; $R_{G(ext)}$ = 1 Ω

Figure 19: Resistive Switching Energy v/s $R_{G(ext)}$ (V_{DD} = 1200V)



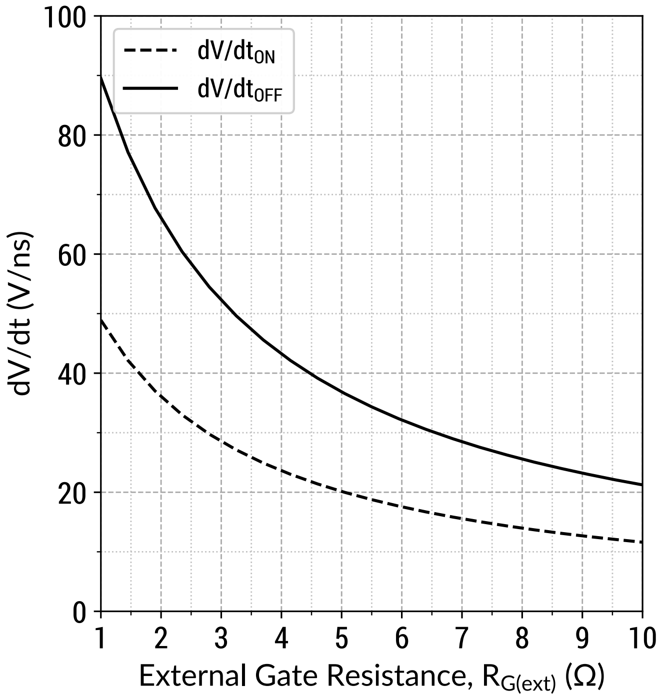
T_j = 25°C; V_{GS} = -5/+15V; I_{DS} = 35 A

Figure 20: Switching Time v/s $R_{G(ext)}$ (V_{DD} = 1200V)



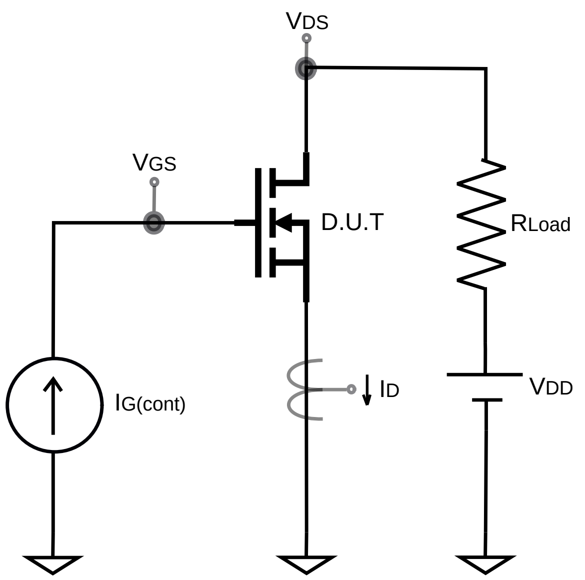
T_j = 25°C; V_{GS} = -5/+15V; I_{DS} = 35 A

Figure 21: dV/dt v/s $R_{G(ext)}$
(V_{DD} = 1200V)

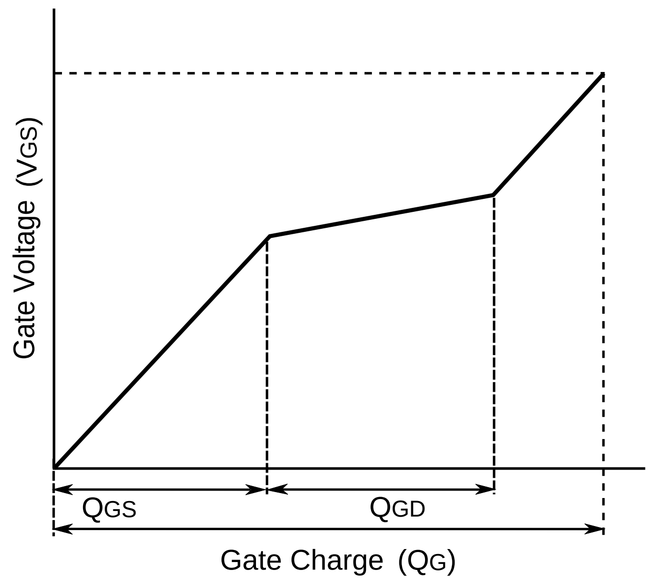


T_j = 25°C; V_{GS} = -5/+15V; I_{DS} = 35 A

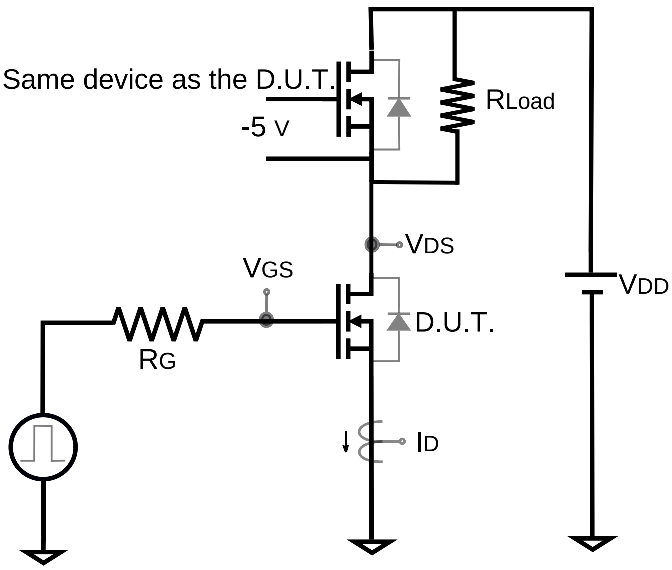
Gate Charge Circuit



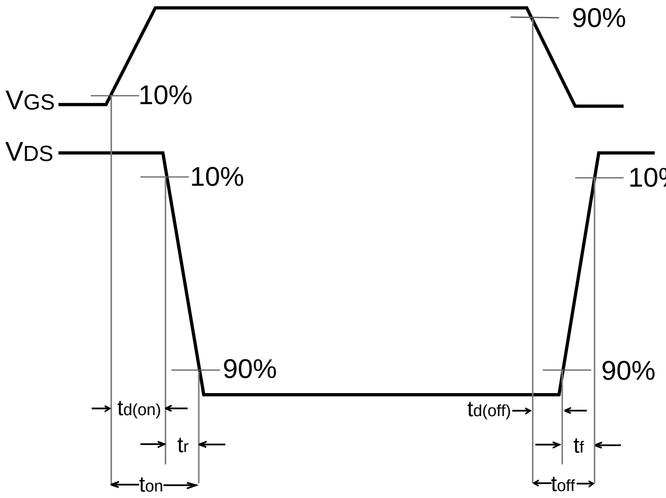
Gate Charge Waveform



Switching Time Circuit

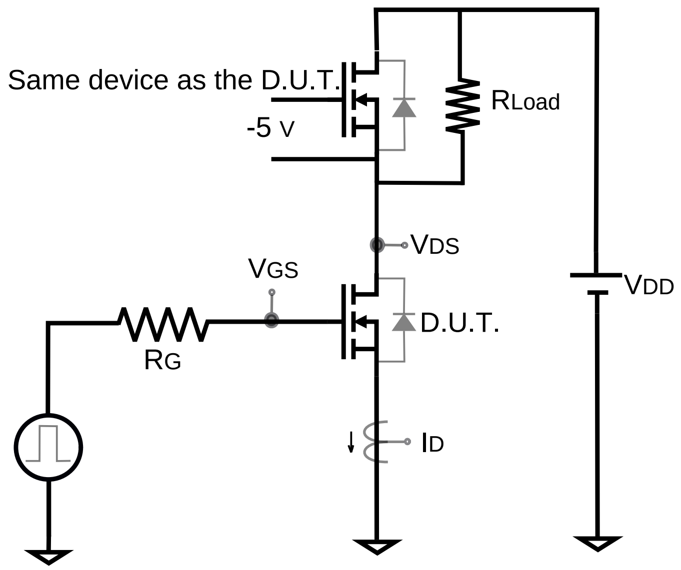


Switching Time Waveform

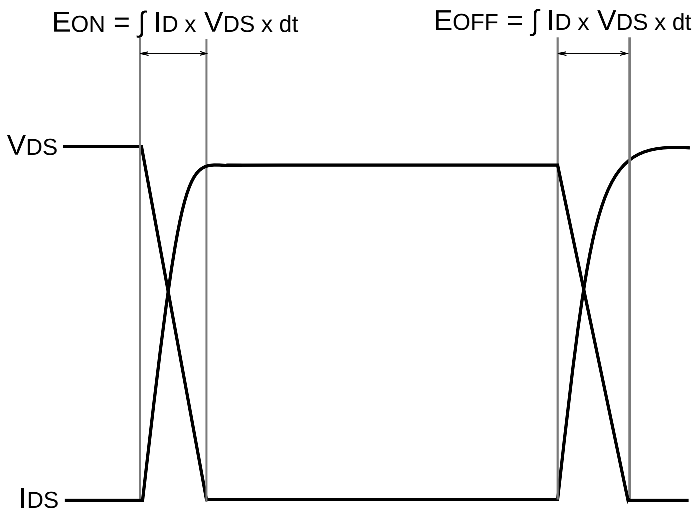


GeneSiC SEMICONDUCTOR

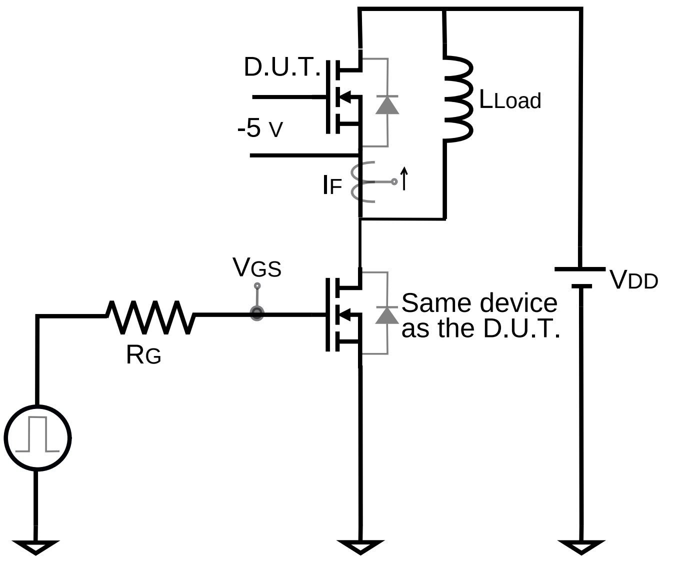
Switching Energy Circuit



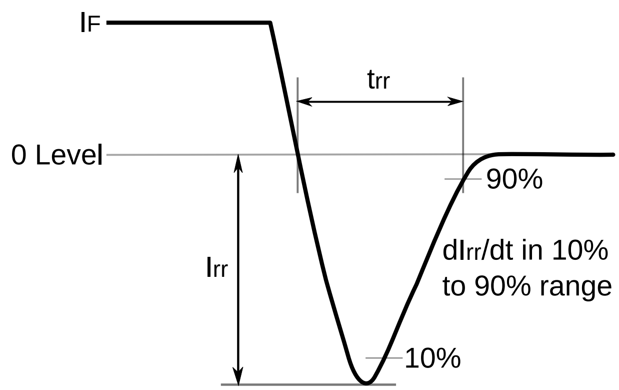
Switching Energy Waveform



Reverse Recovery Circuit



Reverse Recovery Waveform



Mechanical Parameters

This information is confidential, please contact **sales@genesicsemi.com** to learn more.

Chip Dimensions

This information is confidential, please contact **sales@genesicsemi.com** to learn more.

NOTE

1. CONTROLLED DIMENSION IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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Related Links

- SPICE Models: https://www.genesicsemi.com/sic-mosfet/G3R45MT17-CAL/G3R45MT17-CAL_SPICE.zip
- PLECS Models: https://www.genesicsemi.com/sic-mosfet/G3R45MT17-CAL/G3R45MT17-CAL_PLECS.zip
- CAD Models: https://www.genesicsemi.com/sic-mosfet/G3R45MT17-CAL/G3R45MT17-CAL_3D.zip
- Gate Driver Reference: https://www.genesicsemi.com/technical-support
- Evaluation Boards: https://www.genesicsemi.com/technical-support
- Reliability: https://www.genesicsemi.com/reliability
- Compliance: https://www.genesicsemi.com/compliance
- Quality Manual: https://www.genesicsemi.com/quality

Revision History

- Rev 21/Jun: Updated switching time and switching energy data
- Supersedes: Rev 20/Jun, Rev 20/Sep, Rev 21/Feb

www.genesicsemi.com/sic-mosfet/

Published by GeneSiC Semiconductor, Inc.
43670 Trade Center Place Suite 155, Dulles, VA 20166; USA